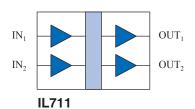
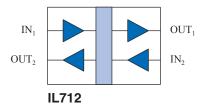
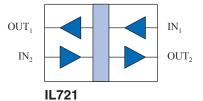


# High Speed Two-Channel Digital Isolators

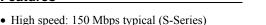
# **Functional Diagrams**







#### **Features**



• High temperature: -40°C to +125°C (T-Series and VE-Series)

• Very high isolation: 6 kV<sub>RMS</sub> Reinforced Isolation (VE-Series)

• High working voltage: 1 kV<sub>RMS</sub> per VDE V 0884-10 (VE-Series)

• 50 kV/µs typ.; 30 kV/µs min. common mode transient immunity · No carrier or clock for low EMI emissions and susceptibility

• 1.2 mA/channel typical quiescent current

• 300 ps typical pulse width distortion (S-Series)

• 100 ps pulse jitter

• 2 ns channel-to-channel skew

• 10 ns typical propagation delay

• 44000 year barrier life

· Excellent magnetic immunity

VDE V 0884-10 certified; UL 1577 recognized

• MSOP, SOIC, PDIP, and True 8 mm creepage packages

#### **Applications**

· Board-to-board communication

CANbus

Peripheral interfaces

Logic level shifting

Equipment covered under IEC 61010-1 Edition 3

• 5 kV<sub>RMS</sub> rated IEC 60601-1 medical applications

#### **Description**

NVE's IL700 family of high-speed digital isolators are CMOS devices manufactured with NVE's patented\* IsoLoop® spintronic Giant Magnetoresistive (GMR) technology. A unique ceramic/polymer composite barrier provides excellent isolation and virtually unlimited barrier life.

The IL711S and IL712S are the world's fastest two-channel isolators, with a 150 Mbps typical data rate for both channels. Standard and S-Grade parts are specified over a temperature range of -40°C to +100°C; "T" and "VE" Grade parts have a maximum operating temperature of 125°C. V-Series versions offer extremely high isolation voltages of 6 kV<sub>RMS</sub> for wide-body packages and 2.5 kV<sub>RMS</sub> for MSOPs.

The symmetric magnetic coupling barrier provides a typical propagation delay of only 10 ns and a pulse width distortion as low as 300 ps (0.3 ns), achieving the best specifications of any isolator. Typical transient immunity of 50 kV/us is unsurpassed.

The IL711 has two transmit channels; the IL712 and IL721 have one transmit and one receive channel. The IL721 has channels reversed to better suit certain board layouts.

The IL711 and IL712 are available in 8-pin MSOP, SOIC, and PDIP packages. The IL711 and IL721 are also available in NVE's unique JEDEC-compliant 16 pin package with True 8 mm creepage under IEC 60601.





**Absolute Maximum Ratings** 

Parameters	Symbol	Min.	Тур.	Max.	Units	<b>Test Conditions</b>
Storage Temperature	$T_s$	-55		150	°C	
Junction Temperature	$T_{\mathrm{J}}$	-55		150	°C	
Ambient Operating Temperature <sup>(1)</sup> IL711T/IL711VE/IL712T/IL721VE	$T_{A}$	-40		100 125	°C	
Supply Voltage	$V_{\mathrm{DD1}},V_{\mathrm{DD2}}$	-0.5		7	V	
Input Voltage	$V_{\rm I}$	-0.5		$V_{DD} + 0.5$	V	
Output Voltage	$V_{o}$	-0.5		$V_{DD} + 0.5$	V	
Output Current Drive	$I_{o}$			10	mA	
Lead Solder Temperature				260	°C	10 sec.
ESD			2		kV	HBM

**Recommended Operating Conditions** 

Parameters	Symbol	Min.	Тур.	Max.	Units	<b>Test Conditions</b>
Ambient Operating Temperature	т	-40		100	°C	
IL711T/IL711VE/IL712T/IL721T/IL721VE	I <sub>A</sub>	-40		125	°C	
Junction Temperature	т	-40		110	°C	
IL711T/IL711VE/IL712T/IL721T/IL721VE	1 ј	-40		125	°C	
Supply Voltage	$V_{DD1}, V_{DD2}$	3.0		5.5	V	
Logic High Input Voltage	$V_{\text{IH}}$	2.4		$V_{DD}$	V	
Logic Low Input Voltage	$V_{\scriptscriptstyle \mathrm{IL}}$	0		0.8	V	
Input Signal Rise and Fall Times	$t_{IR}, t_{IF}$			1	μs	

**Insulation Specifications** 

Parameters	Symbol	Min.	Тур.	Max.	Units	<b>Test Conditions</b>
Creepage Distance (external)		•	<u> </u>			
MSOP8		3.01			mm	
SOIC8		4.03			mm	
PDIP8		7.04			mm	
True 8 <sup>™</sup> 0.3" SOIC16		8.03	8.3		mm	Per IEC 60601
Total Barrier Thickness (internal)		0.012	0.016		mm	
Leakage Current <sup>(5)</sup>			0.2		μΑ	240 V <sub>RMS</sub> , 60 Hz
Barrier Resistance <sup>(5)</sup>	$R_{IO}$		>10 <sup>14</sup>		Ω	500 V
Barrier Capacitance <sup>(5)</sup>	C <sub>IO</sub>		2		pF	f=1 MHz
Comparative Tracking Index	CTI	≥600			$V_{RMS}$	Per IEC 60112
High Voltage Endurance (Maximum Barrier Voltage for Indefinite Life)  AC  DC	$V_{IO}$	1000 1500			$ m V_{RMS}$ $ m V_{DC}$	At maximum operating temperature
Surge Immunity ("VE" Versions)	V <sub>IOSM</sub>	12.8			$kV_{PK}$	Per IEC 61000-4-5
Barrier Life			44000		Years	100°C, 1000 V <sub>RMS</sub> , 60% CL activation energy

# **Thermal Characteristics**

Parameter		Symbol	Min.	Тур.	Max.	Units	<b>Test Conditions</b>	
Junction–Ambient Thermal Resistance	MSOP 0.15" SOIC 0.3" SOIC PDIP	$\theta_{\rm JA}$		80 60 60 60		°C/W	Soldered to double-sided	
Junction–Case (Top) Thermal Resistance	MSOP 0.15" SOIC 0.3" SOIC PDIP	$\Psi_{{\scriptscriptstyle T}}$		40 10 20 20		°C/W	board; free air	
Power Dissipation	MSOP 0.15" SOIC 0.3" SOIC PDIP	$P_{\scriptscriptstyle D}$			500 675 800 800	mW		



#### **Safety and Approvals**

#### **VDE V 0884-10** (VDE V 0884-11 pending)

V-Series (Reinforced Isolation; VDE File Number 5016933-4880-0002)

- Working Voltage (V<sub>IORM</sub>) 1000 V<sub>RMS</sub> (1415 V<sub>PK</sub>); reinforced insulation; pollution degree 2
- Isolation voltage (V<sub>ISO</sub>) 6000 V<sub>RMS</sub>
- Surge immunity (V<sub>IOSM</sub>) 12.8 kV<sub>PK</sub>
- Surge rating 8 kV
- Transient overvoltage (V<sub>IOTM</sub>) 6000 V<sub>PK</sub>
- Each part tested at 2387 V<sub>PK</sub> for 1 second, 5 pC partial discharge limit
- $\bullet$  Samples tested at 6000  $V_{PK}$  for 60 sec.; then 2122  $V_{PK}$  for 10 sec. with 5 pC partial discharge limit

#### Standard versions (Basic Isolation; VDE File Number 5016933-4880-0001)

- Working Voltage ( $V_{IORM}$ ) 600  $V_{RMS}$  (848  $V_{PK}$ ); basic insulation; pollution degree 2
- Isolation voltage  $(V_{ISO})$  2500  $V_{RMS}$
- $\bullet$  Transient overvoltage (V\_{IOTM}) 4000  $V_{PK}$
- Surge rating 4000 V
- Each part tested at 1590 V<sub>PK</sub> for 1 second, 5 pC partial discharge limit
- $\bullet$  Samples tested at 4000  $V_{PK}$  for 60 sec.; then 1358  $V_{PK}$  for 10 sec. with 5 pC partial discharge limit

Safety-Limiting Values	Symbol	Value	Units
Safety rating ambient temperature	$T_{S}$	180	°C
Safety rating power (180°C)	$P_{S}$	270	mW
Supply current safety rating (total of supplies)	$I_S$	54	mA

#### IEC 61010-1 (Edition 2; TUV Certificate Numbers N1502812; N1502812-101)

Reinforced Insulation; Pollution Degree II; Material Group III

Part No.		Working
Suffix	Package	Voltage
-1	MSOP (standard)	$150 V_{RMS}$
V-1	MSOP (high isolation voltage)	$300 V_{RMS}$
-2	PDIP	$300 V_{RMS}$
-3	SOIC	$150 V_{RMS}$
None	0.3" SOIC (standard)	$300 V_{RMS}$
VE	0.3" SOIC (high isolation voltage)	$1000 V_{RMS}$

#### *UL 1577* (Component Recognition Program File Number E207481)

- 1 kV-rated standard MSOPs tested at 1200 V<sub>RMS</sub> (1768 V<sub>PK</sub>) for 1 second; each lot sample tested at 1200 V<sub>RMS</sub> (1768 V<sub>PK</sub>) for 1 minute
- 2.5 kV-rated parts tested at 3000 V<sub>RMS</sub> (4240 V<sub>PK</sub>) for 1 second; each lot sample tested at 2500 V<sub>RMS</sub> (3530 V<sub>PK</sub>) for 1 minute
- 6 kV-rated VE-Series parts tested at 7.2 kV<sub>RMS</sub> (10.2 kV<sub>PK</sub>) for 1 second; each lot sample tested at 6 kV<sub>RMS</sub> (8485 V<sub>PK</sub>) for 1 minute

# **Soldering Profile**

Per JEDEC J-STD-020C, MSL 1



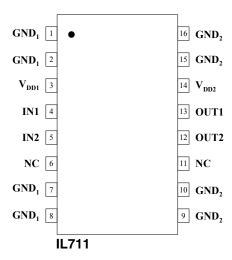
# IL711-1, -2, and -3 Pin Connections

1	$V_{\mathrm{DD1}}$	Supply voltage
2	$IN_1$	Data in, channel 1
3	$IN_2$	Data in, channel 2
4	$GND_1$	Ground return for V <sub>DD1</sub>
5	$GND_2$	Ground return for V <sub>DD2</sub>
6	$OUT_2$	Data out, channel 2
7	$OUT_1$	Data out, channel 1
8	$V_{\mathrm{DD2}}$	Supply voltage

# 

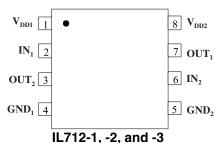
### **IL711 Pin Connections**

1	CND	Ground return for V <sub>DD1</sub>					
2	$GND_1$	(pins 1, 2, 7, and 8 internally connected)					
3	$V_{DD1}$	Supply voltage					
4	$IN_1$	Data in, channel 1					
5	$IN_2$	Data in, channel 2					
6	NC	No connection					
7	GND <sub>1</sub>	Ground return for V <sub>DD1</sub>					
8	GND <sub>1</sub>	(pins 1, 2, 7, and 8 internally connected)					
9	$GND_2$	Ground return for V <sub>DD2</sub>					
10	$OND_2$	(pins 9, 10, 15, and 16 internally connected)					
11	NC	No connection					
12	OUT <sub>2</sub>	Data out, channel 2					
13	$OUT_1$	Data out, channel 1					
14	$V_{\mathrm{DD2}}$	Supply voltage					
15	GND <sub>2</sub>	Ground return for V <sub>DD2</sub>					
16	$OIND_2$	(pins 9, 10, 15, and 16 internally connected)					



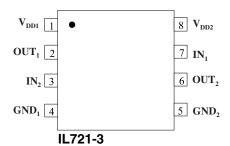
#### IL712-1, -2, and -3 Pin Connections

	, , -	
1	$V_{\mathrm{DD1}}$	Supply voltage
2	$IN_1$	Data in, channel 1
3	OUT <sub>2</sub>	Data out, channel 2
4	$GND_1$	Ground return for V <sub>DD1</sub>
5	$GND_2$	Ground return for V <sub>DD2</sub>
6	$IN_2$	Data in, channel 2
7	$OUT_1$	Data out, channel 1
8	$V_{\mathrm{DD2}}$	Supply voltage



# **IL721-3 Pin Connections**

1	$V_{\mathrm{DD1}}$	Supply voltage
2	OUT <sub>1</sub>	Data out, channel 1
3	$IN_2$	Data in, channel 2
4	$GND_1$	Ground return for V <sub>DD1</sub>
5	GND <sub>2</sub>	Ground return for V <sub>DD2</sub>
6	OUT <sub>2</sub>	Data out, channel 2
7	$IN_1$	Data in, channel 1
8	$V_{\mathrm{DD2}}$	Supply voltage

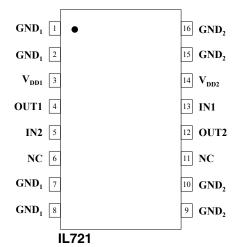






# **IL721 Pin Connections**

1	CND	Ground return for V <sub>DD1</sub>
2	$GND_1$	(pins 1, 2, 7, and 8 internally connected)
3	$V_{DD1}$	Supply voltage
4	$OUT_1$	Data out, channel 1
5	$IN_2$	Data in, channel 2
6	NC	No connection
7	CND	Ground return for V <sub>DD1</sub>
8	$GND_1$	(pins 1, 2, 7, and 8 internally connected)
9	GND <sub>2</sub>	Ground return for V <sub>DD2</sub>
10	$OND_2$	(pins 9, 10, 15, and 16 internally connected)
11	NC	No connection
12	OUT <sub>2</sub>	Data out, channel 2
13	$IN_1$	Data in, channel 1
14	$V_{\mathrm{DD2}}$	Supply voltage
15	GND <sub>2</sub>	Ground return for V <sub>DD2</sub>
16	$OND_2$	(pins 9, 10, 15, and 16 internally connected)





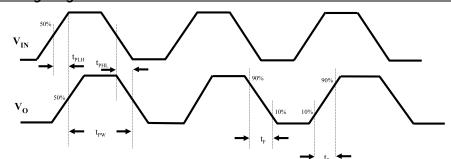


3.3 Volt Electrical Specifications ( $T_{min}$ to $T_{max}$ unless otherwise stated)									
Parameters	Symbol	Min.	Тур.	Max.	Units	<b>Test Conditions</b>			
Input Quiescent Supply Current									
IL711	T		8	10	μΑ				
IL712/IL721	$I_{\mathrm{DD1}}$		1.2	1.75	mA				
Output Quiescent Supply Current	Output Quiescent Supply Current								
IL711	т		2.4	3.5	mA				
IL712/IL721	$I_{\mathrm{DD2}}$		1.2	1.75	mA				
Logic Input Current	$I_{\rm I}$	-10		10	μΑ				
Logic High Output Voltage	$V_{\mathrm{OH}}$	$V_{DD} - 0.1$	$V_{ m DD}$		V	$I_{O} = -20 \mu A, V_{I} = V_{IH}$			
Logic High Output Voluge	▼ OH	$0.8 \times V_{DD}$	$0.9 \times V_{DD}$		•	$I_O = -4 \text{ mA}, V_I = V_{IH}$			
Logic Low Output Voltage	$V_{OL}$		0	0.1	V	$I_0 = 20 \mu A, V_I = V_{IL}$			
Logic Low Output Voltage	v <sub>OL</sub>		0.5	0.8	•	$I_O = 4 \text{ mA}, V_I = V_{IL}$			

Switching Specifications ( $V_{DD} = 3.3 \text{ V}$ )						
Maximum Data Rate						
IL711/IL712/IL721		100	110		Mbps	$C_L = 15 \text{ pF}$
IL711S/IL712S		130	140		Mbps	$C_L = 15 \text{ pF}$
IL711T/IL712T/IL721T		100	110		Mbps	$C_L = 15 \text{ pF}$
Pulse Width <sup>(7)</sup>	PW	10	7.5		ns	50% Points, V <sub>o</sub>
Propagation Delay Input to Output (High to Low)	$t_{ m PHL}$		12	18	ns	$C_L = 15 \text{ pF}$
Propagation Delay Input to Output (Low to High)	$t_{\rm PLH}$		12	18	ns	$C_L = 15 \text{ pF}$
Pulse Width Distortion <sup>(2)</sup>						
IL711/IL712/IL721			2	3	ns	$C_L = 15 \text{ pF}$
IL711S/IL712S	PWD		2	3	ns	$C_L = 15 \text{ pF}$
IL711T/IL712T/IL721T			1	3	ns	$C_L = 15 \text{ pF}$
Propagation Delay Skew <sup>(3)</sup>	$t_{PSK}$		4	6	ns	$C_L = 15 \text{ pF}$
Output Rise Time (10%–90%)	$t_{R}$		2	4	ns	$C_L = 15 \text{ pF}$
Output Fall Time (10%–90%)	$t_{\mathrm{F}}$		2	4	ns	$C_L = 15 \text{ pF}$
Common Mode Transient Immunity (Output Logic High or Logic Low) <sup>(4)</sup>	$ CM_H ,  CM_L $	30	50		kV/μs	$V_{CM} = 1500 V_{DC}$ $t_{TRANSIENT} = 25 \text{ ns}$
Channel-to-Channel Skew	$t_{CSK}$		2	3	ns	$C_L = 15 \text{ pF}$
Dynamic Power Consumption <sup>(6)</sup>			140	240	μA/Mbps	per channel

Magnetic Field Immunity <sup>(8)</sup> (V <sub>DD2</sub> = 3V, 3V <v<sub>DD1&lt;5.5V)</v<sub>							
Power Frequency Magnetic Immunity	$H_{PF}$	1000	1500		A/m	50Hz/60Hz	
Pulse Magnetic Field Immunity	$H_{PM}$	1800	2000		A/m	$t_p = 8 \mu s$	
Damped Oscillatory Magnetic Field	$H_{OSC}$	1800	2000		A/m	0.1Hz – 1MHz	
Cross-axis Immunity Multiplier <sup>(9)</sup>	$K_{X}$		2.5				

# **Timing Diagram**



Lea	6	n	d
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$t_{\scriptscriptstyle PLH}$	Propagation Delay, Low to High
$t_{\mathrm{PHL}}$	Propagation Delay, High to Low
$t_{\mathrm{PW}}$	Minimum Pulse Width
$t_R$	Rise Time
t <sub>r</sub>	Fall Time





<b>5 Volt Electrical Specifications</b> (T <sub>min</sub> to T <sub>max</sub> unless otherwise stated)								
Parameters	Symbol	Min.	Тур.	Max.	Units	<b>Test Conditions</b>		
Input Quiescent Supply Current								
IL711	T		10	15	μΑ			
IL712/IL721	$I_{\mathrm{DD1}}$		1.8	2.5	mA			
Output Quiescent Supply Current								
IL711	ī		3.6	5	mA			
IL712/IL721	$I_{\mathrm{DD2}}$		1.8	2.5	mA			
Logic Input Current	$I_{I}$	-10		10	μΑ			
Logic High Output Voltage	V <sub>OH</sub>	$V_{\rm DD} - 0.1$	$V_{ m DD}$		V	$I_{O} = -20 \mu A, V_{I} = V_{IH}$		
Logic High Output Voltage		$0.8 \times V_{DD}$	$0.9 \times V_{DD}$		*	$I_O = -4 \text{ mA}, V_I = V_{IH}$		
Logic Low Output Voltage	$V_{OL}$		0	0.1	V	$I_0 = 20 \mu A, V_I = V_{IL}$		
Logic Low Output Voltage	V OL		0.5	0.8	•	$I_O = 4 \text{ mA}, V_I = V_{IL}$		

Switching Specifications ( $V_{DD} = 5 \text{ V}$ )						
Maximum Data Rate						
IL711/IL712/IL721		100	110		Mbps	$C_L = 15 \text{ pF}$
IL711S/IL712S		130	150		Mbps	$C_L = 15 \text{ pF}$
IL711T/IL712T/IL721T		100	110		Mbps	$C_L = 15 \text{ pF}$
Pulse Width <sup>(7)</sup>	PW	10	7.5		ns	50% Points, V <sub>o</sub>
Propagation Delay Input to Output (High to Low)	$t_{PHL}$		10	15	ns	$C_L = 15 \text{ pF}$
Propagation Delay Input to Output (Low to High)	$t_{\rm PLH}$		10	15	ns	$C_L = 15 \text{ pF}$
Pulse Width Distortion <sup>(2)</sup>						
IL711/IL712/IL721			2	3	ns	$C_L = 15 \text{ pF}$
IL711S/IL712S	PWD		2	3	ns	$C_L = 15 \text{ pF}$
IL711T/IL712T/IL721T			0.3	3	ns	$C_L = 15 \text{ pF}$
Pulse Jitter <sup>(10)</sup>	$t_{ m J}$		100		ps	$C_L = 15 \text{ pF}$
Propagation Delay Skew <sup>(3)</sup>	$t_{PSK}$		4	6	ns	$C_L = 15 \text{ pF}$
Output Rise Time (10%–90%)	$t_{R}$		1	3	ns	$C_L = 15 \text{ pF}$
Output Fall Time (10%–90%)	$t_{\mathrm{F}}$		1	3	ns	$C_L = 15 \text{ pF}$
Common Mode Transient Immunity	$ CM_H ,  CM_L $	30	50		kV/μs	$V_{CM} = 1500 V_{DC}$
(Output Logic High or Logic Low) <sup>(4)</sup>		30	30		κ τ/μ3	$t_{\text{TRANSIENT}} = 25 \text{ ns}$
Channel to Channel Skew	$t_{\rm CSK}$		2	3	ns	$C_L = 15 \text{ pF}$
Dynamic Power Consumption <sup>(6)</sup>			200	340	μA/Mbps	per channel

Magnetic Field Immunity <sup>(8)</sup> (V <sub>DD2</sub> = 5V, 3V <v<sub>DD1&lt;5.5V)</v<sub>						
Power Frequency Magnetic Immunity	$H_{PF}$	2800	3500		A/m	50Hz/60Hz
Pulse Magnetic Field Immunity	$H_{PM}$	4000	4500		A/m	$t_p = 8 \mu s$
Damped Oscillatory Magnetic Field	$H_{OSC}$	4000	4500		A/m	0.1Hz – 1MHz
Cross-axis Immunity Multiplier <sup>(9)</sup>	$K_{X}$		2.5			

#### **Notes** (apply to both 3.3 V and 5 V specifications):

- 1. Absolute maximum ambient operating temperature means the device will not be damaged if operated under these conditions. It does not guarantee performance.
- 2. PWD is defined as  $|t_{PHL} t_{PLH}|$ . %PWD is equal to PWD divided by pulse width.
- 3.  $t_{PSK}$  is the magnitude of the worst-case difference in  $t_{PHL}$  and/or  $t_{PLH}$  between devices at 25°C.
- 4.  $CM_H$  is the maximum common mode voltage slew rate that can be sustained while maintaining  $V_0 > 0.8 V_{DD2}$ .  $CM_L$  is the maximum common mode input voltage that can be sustained while maintaining  $V_0 < 0.8 V$ . The common mode voltage slew rates apply to both rising and falling common mode voltage edges.
- 5. Device is considered a two terminal device: pins 1–4 shorted and pins 5–8 shorted.
- 6. Dynamic power consumption is calculated per channel and is supplied by the channel's input side power supply.
- 7. Minimum pulse width is the minimum value at which specified PWD is guaranteed.
- 8. The relevant test and measurement methods are given in the Electromagnetic Compatibility section on p. 6.
- 9. External magnetic field immunity is improved by this factor if the field direction is "end-to-end" rather than to "pin-to-pin" (see diagram on p. 6).
- 10. 64k-bit pseudo-random binary signal (PRBS) NRZ bit pattern with no more than five consecutive 1s or 0s; 800 ps transition time.





#### **Application Information**

# **Electrostatic Discharge Sensitivity**

This product has been tested for electrostatic sensitivity to the limits stated in the specifications. However, NVE recommends that all integrated circuits be handled with appropriate care to avoid damage. Damage caused by inappropriate handling or storage could range from performance degradation to complete failure.

# **Electromagnetic Compatibility**

IsoLoop Isolators have the lowest EMC footprint of any isolation technology. IsoLoop Isolators' Wheatstone bridge configuration and differential magnetic field signaling ensure excellent EMC performance against all relevant standards.

These isolators are fully compliant with generic EMC standards EN50081, EN50082-1 and the umbrella line-voltage standard for Information Technology Equipment (ITE) EN61000. NVE has completed compliance tests in the categories below:

EN50081-1

Residential, Commercial & Light Industrial Methods EN55022, EN55014

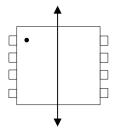
EN50082-2: Industrial Environment

Methods EN61000-4-2 (ESD), EN61000-4-3 (Electromagnetic Field Immunity), EN61000-4-4 (Electrical Transient Immunity), EN61000-4-6 (RFI Immunity), EN61000-4-8 (Power Frequency Magnetic Field Immunity), EN61000-4-9 (Pulsed Magnetic Field), EN61000-4-10 (Damped Oscillatory Magnetic Field) ENV50204

Radiated Field from Digital Telephones (Immunity Test)

Immunity to external magnetic fields is even higher if the field direction is "end-to-end" rather than to "pin-to-pin" as shown in the diagram below:

Cross-axis Field Direction



#### **Dynamic Power Consumption**

IsoLoop Isolators achieve their low power consumption from the way they transmit data across the isolation barrier. By detecting the edge transitions of the input logic signal and converting these to narrow current pulses, a magnetic field is created around the GMR Wheatstone bridge. Depending on the direction of the magnetic field, the bridge causes the output comparator to switch following the input logic signal. Since the current pulses are narrow, about 2.5 ns, the power consumption is independent of mark-to-space ratio and solely dependent on frequency. This has obvious advantages over optocouplers, which have power consumption heavily dependent on mark-to-space ratio.

### **Power Supply Decoupling**

Both power supplies to these devices should be decoupled with low-ESR 47 nF ceramic capacitors. Ground planes for both GND<sub>1</sub> and GND<sub>2</sub> are highly recommended for data rates above 10 Mbps. Capacitors must be located as close as possible to the  $V_{DD}$  pins.

#### **Maintaining Creepage**

Creepage distances are often critical in isolated circuits. In addition to meeting JEDEC standards, NVE isolator packages have unique creepage specifications. Standard pad libraries often extend under the package, compromising creepage and clearance. Similarly, ground planes, if used, should be spaced to avoid compromising clearance. Package drawings and recommended pad layouts are included in this datasheet.

#### Signal Status on Start-up and Shut Down

To minimize power dissipation, input signals are differentiated and then latched on the output side of the isolation barrier to reconstruct the signal. This could result in an ambiguous output state depending on power up, shutdown and power loss sequencing. Unless the circuit connected to the isolator performs its own power- on reset (POR), a start-up initialization circuit should be considered. Initialization consists of toggling the input either high then low, or low then high.

In CAN applications, the IL712 or IL721 should be used with CAN transceivers with Dominant Timeout functions for seamless POR. Most CAN transceivers have Dominant Timeout options. Examples include NXP's TJA 1050 and TJA 1040 transceivers.

#### **Data Transmission Rates**

The reliability of a transmission system is directly related to the accuracy and quality of the transmitted digital information. For a digital system, those parameters which determine the limits of the data transmission are pulse width distortion and propagation delay skew.

Propagation delay is the time taken for the signal to travel through the device. This is usually different when sending a low-to-high than when sending a high-to-low signal. This difference, or error, is called pulse width distortion (PWD) and is usually in nanoseconds. It may also be expressed as a percentage:

For example, with data rates of 12.5 Mbps:  

$$PWD\% = \frac{3 \text{ ns}}{80 \text{ ns}} \times 100\% = 3.75\%$$

This figure is almost **three times** better than any available optocoupler with the same temperature range, and two times better than any optocoupler regardless of published temperature range. IsoLoop isolators exceed the 10% maximum PWD recommended by PROFIBUS, and will run to nearly 35 Mb within the 10% limit.

Propagation delay skew is the signal propagation difference between two or more channels. This becomes significant in clocked systems because it is undesirable for the clock pulse to arrive before the data has settled. Propagation delay skew is especially critical in high data rate parallel systems for establishing and maintaining accuracy and repeatability. Worst-case channel-to-channel skew in an IL700 Isolator is just 3 nsten times better than any optocoupler. IL700 Isolators have a maximum propagation delay skew of 6 ns—five times better than any optocoupler.



#### **Illustrative Applications**

NVE offers a unique line of single-chip isolated RS-485, PROFIBUS, and CAN transceivers, but as illustrated in the circuits below, IL700-Series Isolators can also be used as part of multi-chip designs with non-isolated transceivers:

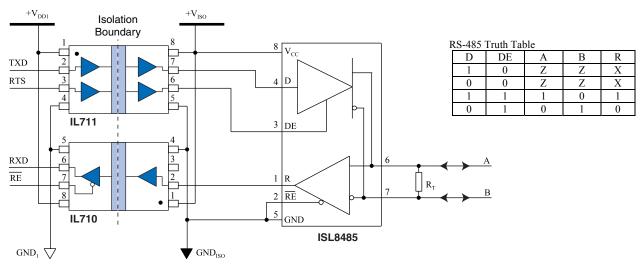


Figure 1. Isolated PROFIBUS / RS-485 circuit.

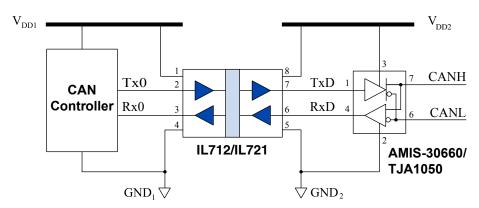


Figure 2. Isolated CAN circuit.

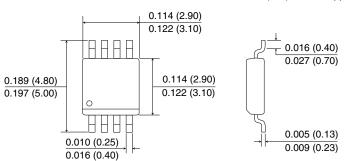
CAN isolation is increasingly necessary to reduce EMI susceptibility, especially in high-speed applications and in hybrid and electrical vehicle networks, where the 12 V battery has been replaced with one of several hundred volts. Operator and equipment safety becomes critical when a high voltage source, such as the battery, needs to be connected to diagnosis systems during routine maintenance procedures. In the application shown above, the microcontroller is isolated from the CAN transceiver by an IL712 or IL721, allowing higher speed and more reliable bus operation by eliminating ground loops and reducing susceptibility to noise and EMI events. The best-in-class 10 ns typical IL712/IL721 propagation delay minimizes CAN loop delay and maximizes data rate over any given bus length. This simple circuit works with any CAN transceiver with a TxD dominant timeout, which includes all of the current-generation transceivers.

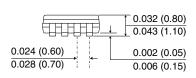


#### **Package Drawings**

#### 8-pin MSOP (-1 suffix)

#### Dimensions in inches (mm); scale = approx. 5X

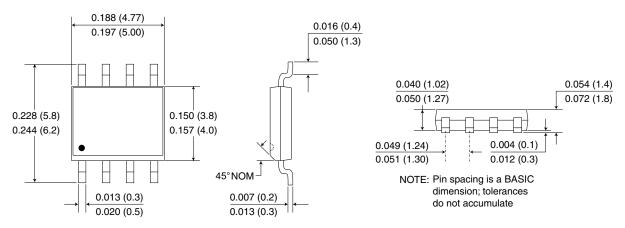




NOTE: Pin spacing is a BASIC dimension; tolerances do not accumulate

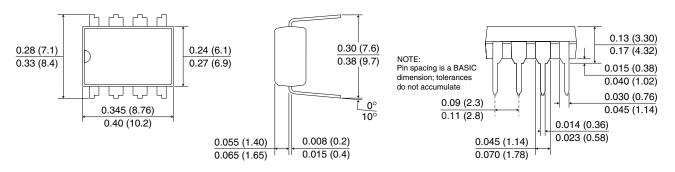
# 8-pin SOIC Package (-3 suffix)

Dimensions in inches (mm); scale = approx. 5X



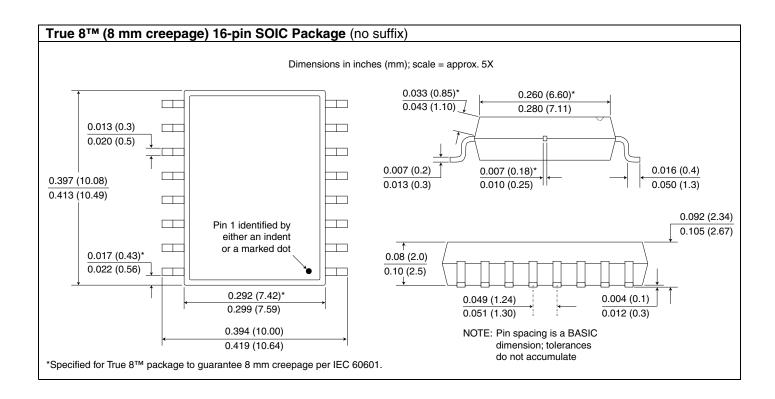
#### 8-pin PDIP (-2 suffix)

Dimensions in inches (mm); scale = approx. 2.5X



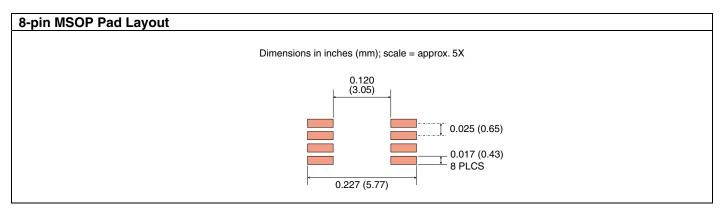


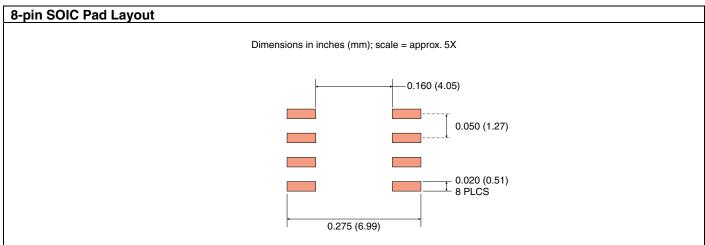


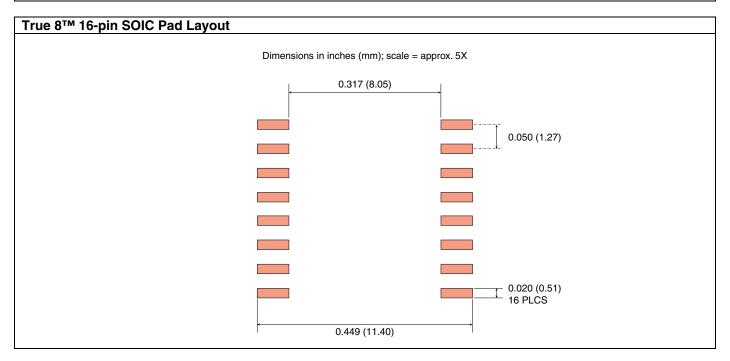




# **Recommended Pad Layouts**



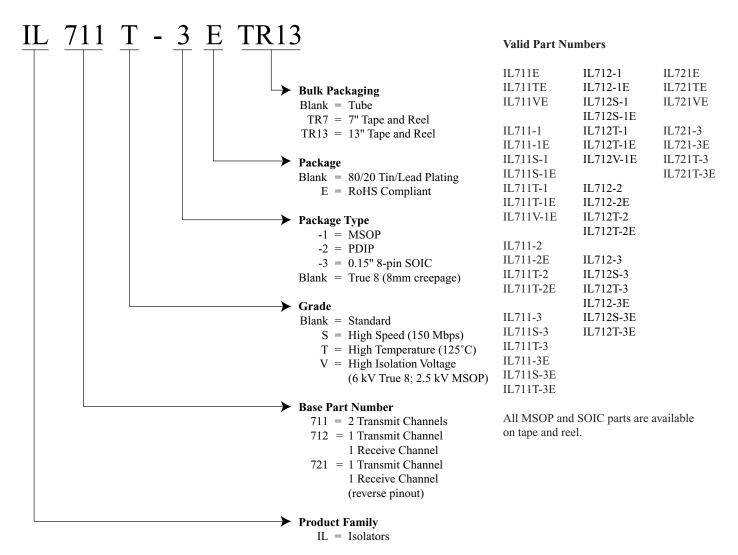








# **Ordering Information**







# **Available Parts**

					Isolation		
Available	Transmit	Receive		Maximum	Voltage		
Parts	Channels	Channels	Mbps	Temperature	(RMS)	Package	RoHS
IL711-1E	2	0	110	100°C	1 kV	MSOP-8	Y
IL711-2	2	0	110	100°C	2.5 kV	PDIP-8	N
IL711-2E	2	0	110	100°C	2.5 kV	PDIP-8	Y
IL711-3	2	0	110	100°C	2.5 kV	SOIC-8	N
IL711-3E	2	0	110	100°C	2.5 kV	SOIC-8	Y
IL711S-1E	2	0	150	100°C	1 kV	MSOP-8	Y
IL711S-3E	2	0	150	100°C	2.5 kV	SOIC-8	Y
IL711T-1E	2	0	110	125°C	1 kV	MSOP-8	Y
IL711T-2	2	0	110	125°C	2.5 kV	PDIP-8	N
IL711T-2E	2	0	110	125°C	2.5 kV	PDIP-8	Y
IL711T-3	2	0	110	125°C	2.5 kV	SOIC-8	N
IL711T-3E	2	0	110	125°C	2.5 kV	SOIC-8	Y
IL711V-1E	2	0	110	100°C	2.5 kV	MSOP-8	Y
IL711VE	2	0	110	125°C	6 kV	True8	Y
IL712-1E	1	1	110	100°C	1 kV	MSOP-8	Y
IL712-2	1	1	110	100°C	2.5 kV	PDIP-8	N
IL712-2E	1	1	110	100°C	2.5 kV	PDIP-8	Y
IL712-3	1	1	110	100°C	2.5 kV	SOIC-8	N
IL712-3E	1	1	110	100°C	2.5 kV	SOIC-8	Y
IL712S-1E	1	1	150	100°C	1 kV	MSOP-8	Y
IL712S-3E	1	1	150	100°C	2.5 kV	SOIC-8	Y
IL712T-1E	1	1	110	125°C	1 kV	MSOP-8	Y
IL712T-2	1	1	110	125°C	2.5 kV	PDIP	N
IL712T-2E	1	1	110	125°C	2.5 kV	PDIP	Y
IL712T-3	1	1	110	125°C	2.5 kV	SOIC-8	N
IL712T-3E	1	1	110	125°C	2.5 kV	SOIC-8	Y
IL712V-1E	1	1	110	100°C	2.5 kV	MSOP	Y
IL721-3E	1	1	110	105°C	2.5 kV	SOIC-8	Y
IL721E	1	1	110	100°C	2.5 kV	True8	Y
IL721T-3E	1	1	110	125°C	2.5 kV	SOIC-8	Y
IL721VE	1	1	110	125°C	6 kV	True8	Y

All MSOP and SOIC part types are available on tape and reel.





ISB-DS-001-IL711/12-AJ November 2016	<ul><li>Changes</li><li>Updated VDE Reinforced Isolation file number and description.</li></ul>
ISB-DS-001-IL711/12-AI	<ul><li>Changes</li><li>Updated VDE certification standard to VDE V 0884-10.</li></ul>
	<ul> <li>Upgraded "VE" Version Surge Immunity specification to 12.8 kV.</li> </ul>
	<ul> <li>Upgraded "VE" Version VDE 0884-10 rating to reinforced insulation.</li> </ul>
ISB-DS-001-IL711/12-AH	Changes
13B-D3-001-1L711/12-AH	Increased V-Series isolation voltage to 6 kVrms.
	<ul> <li>Increased typ. Total Barrier Thickness specification to 0.016 mm.</li> </ul>
	<ul> <li>Increased CTI min. specification to ≥600 V<sub>RMS</sub>.</li> </ul>
ISB-DS-001-IL711/12-AG	Changes
	<ul> <li>Added V-Series high isolation voltage versions (5 kV True 8 and 2.5 kV MSOP).</li> </ul>
	More detailed "Available Parts" table.
ISB-DS-001-IL711/12-AF	<ul><li>Changes</li><li>Added product illustrations to first page.</li></ul>
	<ul> <li>Revised and added details to thermal characteristic specifications (p. 2).</li> </ul>
	<ul> <li>Added VDE 0884 Safety-Limiting Values (p. 3).</li> </ul>
ISB-DS-001-IL711/12-AE	Changes  • IEC 60747-5-5 (VDE 0884) certification.
ISB-DS-001-IL711/12-AD	Changes
	Tighter quiescent current specifications.
	• Upgraded from MSL 2 to MSL 1.
ISB-DS-001-IL711/12-AC	<ul> <li>Changes</li> <li>Increased transient immunity specifications based on additional data.</li> </ul>
	<ul> <li>Increased transient immunity specifications based on additional data.</li> <li>Added VDE 0884 information.</li> </ul>
	<ul> <li>Added vbb voltage endurance specification.</li> </ul>
	<ul> <li>Increased magnetic immunity specifications.</li> </ul>
	Updated package drawings.
	Added recommended solder pad layouts.
ISB-DS-001-IL711/12-AB	
ISB-DS-001-IL/ 11/12-AB	<ul><li>Changes</li><li>Added wide-body package option.</li></ul>
	<ul> <li>VDE0884 compliance pending.</li> </ul>
	Added recommended solder pad layouts.
ISB-DS-001-IL711/12-AA	Changes
	<ul> <li>Detailed isolation and barrier specifications.</li> </ul>
	Cosmetic changes.
ISB-DS-001-IL711/12-Z	Changes

Tightened IL711 typ. output quiescent supply spec. from 3.3 mA to 3 mA at 3.3 V.





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ISB-DS-001-IL711/12-AJ

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